

Description

The SX80P04D uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as 4.5V. This device is suitable for use as a Battery protection or in other Switching application.

General Features

$V_{DS} = -40V$ $I_D = -80 A$

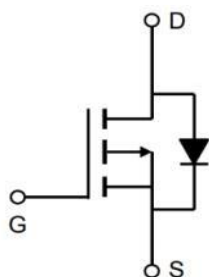
$R_{DS(ON)} < -10m\Omega$ @ $V_{GS} = -10V$

Application

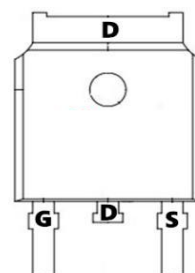
Battery protection

Load switch

Uninterruptible power supply



TO-252-3L



Absolute Maximum Ratings (TC=25°C unless otherwise noted)

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	-40	V
V_{GS}	Gate-Source Voltage	± 20	V
$I_D @ T_C = 25^\circ C$	Continuous Drain Current, $V_{GS} @ -10V^1$	-80	A
$I_D @ T_C = 100^\circ C$	Continuous Drain Current, $V_{GS} @ -10V^1$	-56	A
I_{DM}	Pulsed Drain Current ²	-280	A
EAS	Single Pulse Avalanche Energy ³	500	mJ
I_{AS}	Avalanche Current	-50	A
$P_D @ T_C = 25^\circ C$	Total Power Dissipation ⁴	52.1	W
T_{STG}	Storage Temperature Range	-55 to 150	$^\circ C$
T_J	Operating Junction Temperature Range	-55 to 150	$^\circ C$
$R_{\theta JA}$	Thermal Resistance Junction-Ambient ¹	62	$^\circ C/W$
$R_{\theta JC}$	Thermal Resistance Junction-Case ¹	2.4	$^\circ C/W$

Electrical Characteristics (T_J=25°C, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =-250uA	-40	-44	---	V
$\Delta BV_{DSS}/\Delta T_J$	BV _{DSS} Temperature Coefficient	Reference to 25°C, I _D =-1mA	---	-0.023	---	V/°C
R _{DS(ON)}	Static Drain-Source On-Resistance ²	V _{GS} =-10V, I _D =-12A	---	7.0	10	mΩ
		V _{GS} =-4.5V, I _D =-12A	---	9.0	15	
V _{GS(th)}	Gate Threshold Voltage	V _{GS} =V _{DS} , I _D =-250uA	-1.2	-1.8	-2.5	V
I _{DSS}	Drain-Source Leakage Current	V _{DS} =-40V, V _{GS} =0V, T _J =25°C	---	---	1	uA
		V _{DS} =-40V, V _{GS} =0V, T _J =55°C	---	---	5	
I _{GSS}	Gate-Source Leakage Current	V _{GS} =±20V, V _{DS} =0V	---	---	±100	nA
g _{fs}	Forward Transconductance	V _{DS} =-15V, I _D =-12A	---	20	---	S
R _g	Gate Resistance	V _{DS} =0V, V _{GS} =0V, f=1MHz	---	7	14	Ω
Q _g	Total Gate Charge (-4.5V)	V _{DS} =-20V, V _{GS} =-10V, I _D =-12A	---	27.9	---	nC
Q _{gs}	Gate-Source Charge		---	7.7	---	
Q _{gd}	Gate-Drain Charge		---	7.5	---	
T _{d(on)}	Turn-On Delay Time	V _{DD} =-20V, V _{GS} =-10V, R _G =3.0Ω, I _D =-12A	---	40	---	ns
T _r	Rise Time		---	35.2	---	
T _{d(off)}	Turn-Off Delay Time		---	100	---	
T _f	Fall Time		---	9.6	---	
C _{iss}	Input Capacitance	V _{DS} =-20V, V _{GS} =0V, f=1MHz	---	6500	---	pF
C _{oss}	Output Capacitance		---	790	---	
C _{rss}	Reverse Transfer Capacitance		---	605	---	
I _S	Continuous Source Current ^{1,5}	V _G =V _D =0V, Force Current	---	---	-70	A
V _{SD}	Diode Forward Voltage ²	V _{GS} =0V, I _S =-1A, T _J =25°C	---	---	-1.2	V

Note :

- 1、The data tested by surface mounted on a 1 inch² FR-4 board with 2OZ copper.
- 2、The data tested by pulsed, pulse width ≤ 300us, duty cycle ≤ 2%
- 3、The EAS data shows Max. rating. The test condition is V_{DD}=-32V, V_{GS}=-10V, L=0.1mH, I_{AS}=-50A
- 4、The power dissipation is limited by 150°C junction temperature
- 5、The data is theoretically the same as I_D and I_{DM}, in real applications, should be limited by total power dissipation.

Typical Characteristics

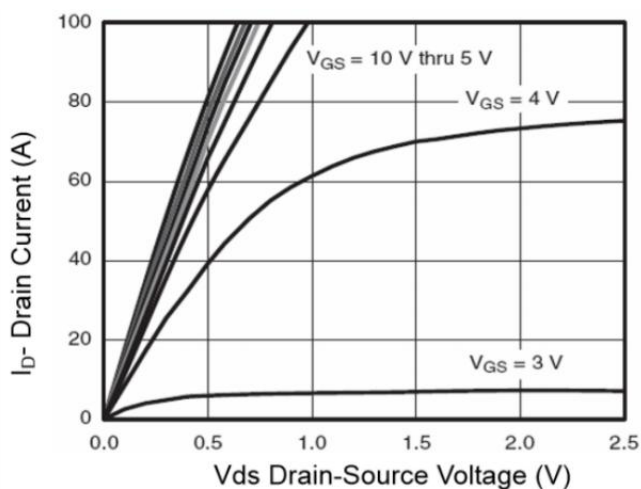


Figure 1 Output Characteristics

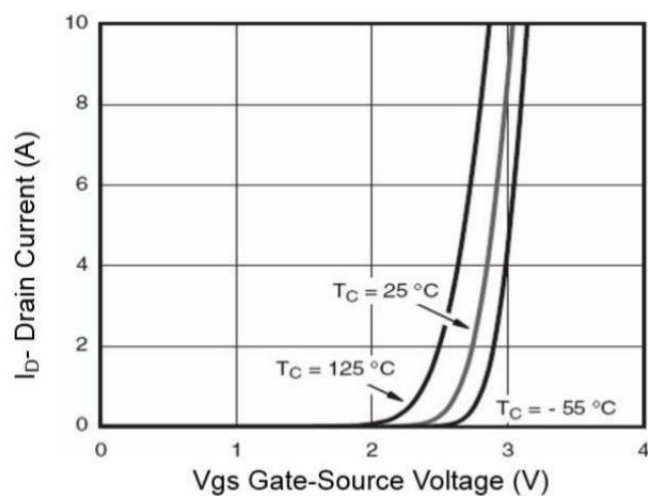


Figure 2 Transfer Characteristics

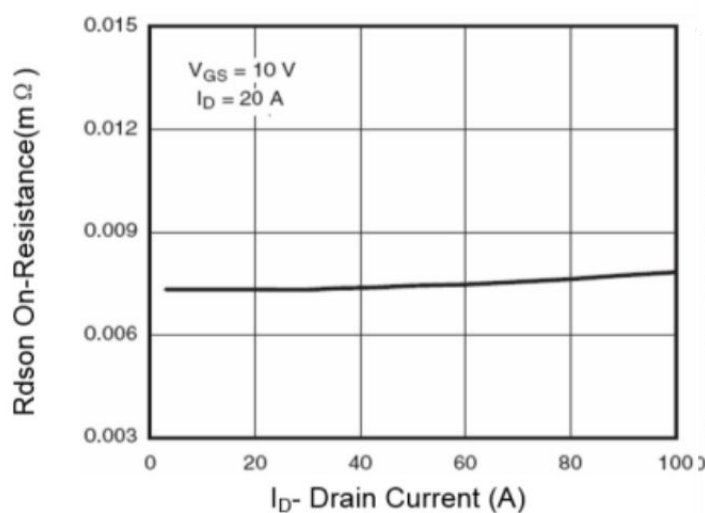


Figure 3 Rdson- Drain Current

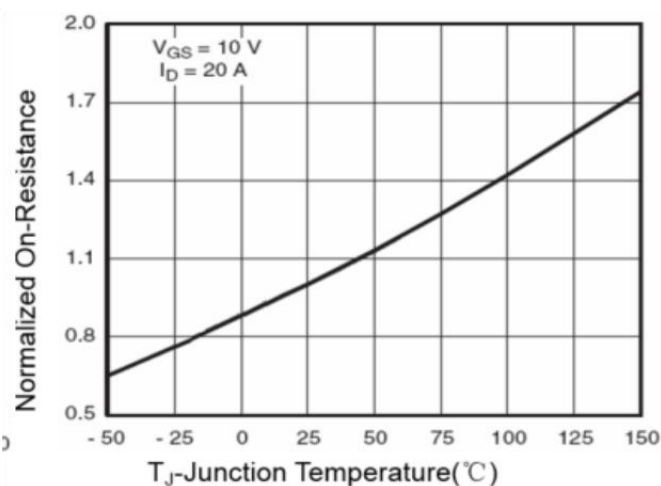


Figure 4 Rdson-Junction Temperature

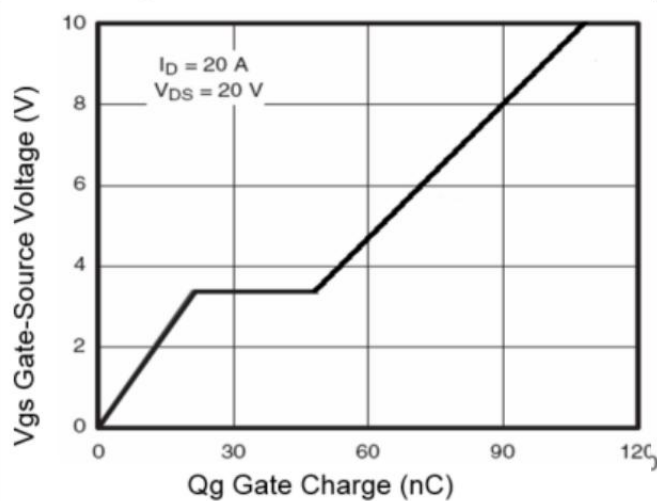


Figure 5 Gate Charge

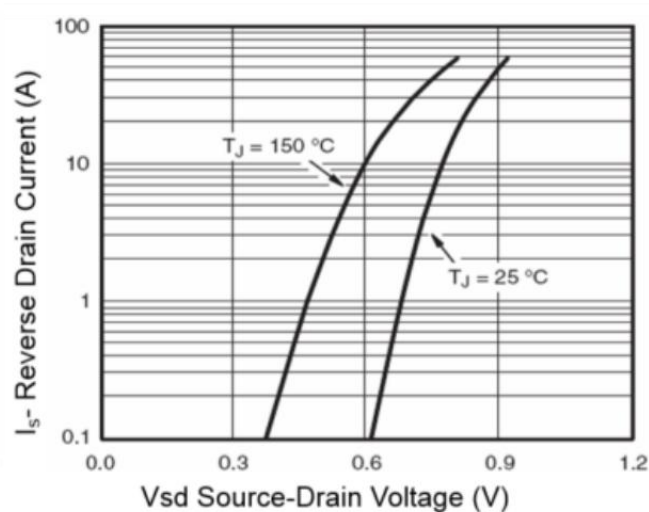


Figure 6 Source- Drain Diode Forward

Typical Characteristics

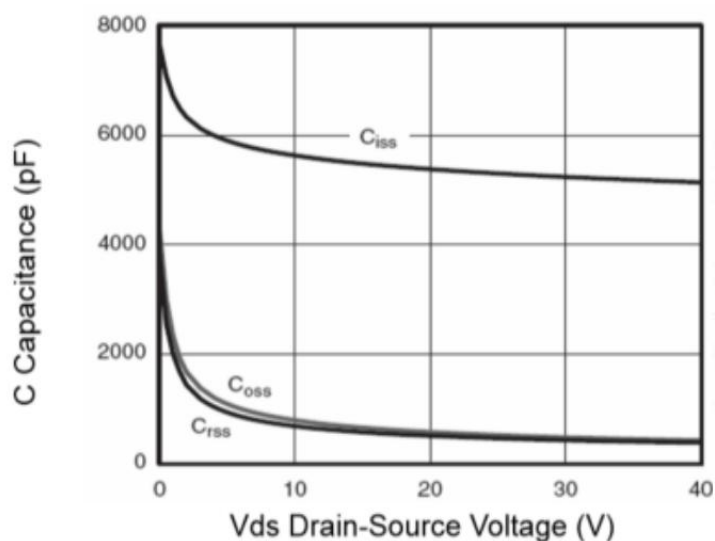


Figure 7 Capacitance vs Vds

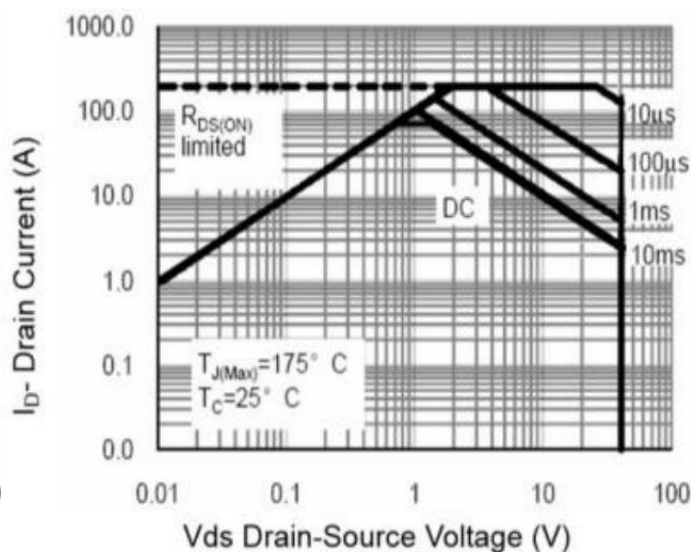


Figure 8 Safe Operation Area

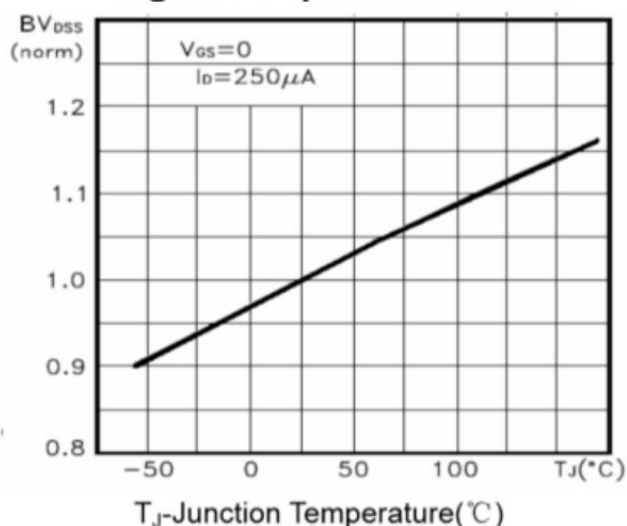


Figure 9 BV_{DSS} vs Junction Temperature

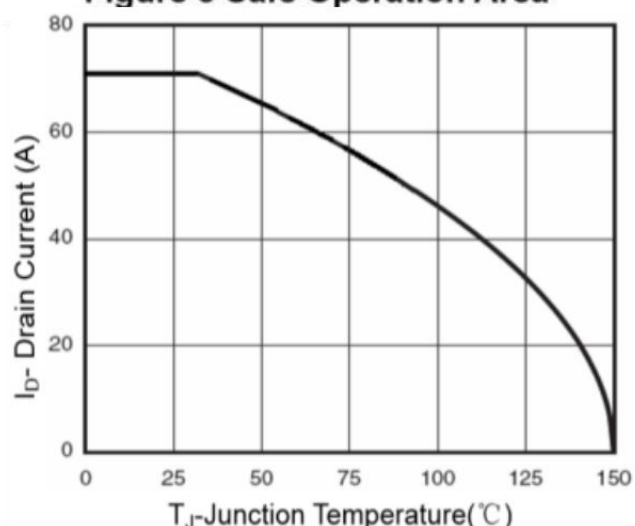


Figure 10 ID Current Derating vs Junction Temperature

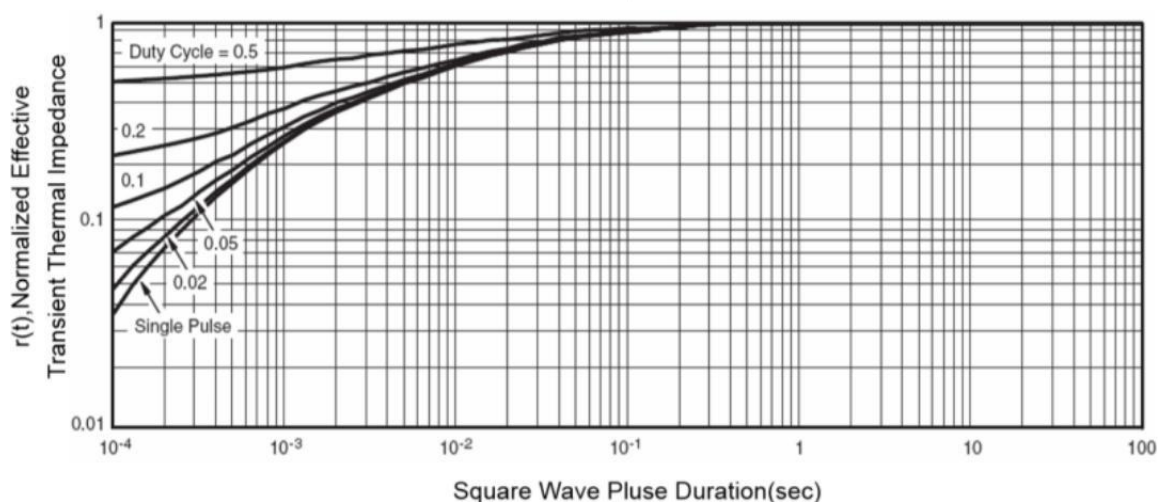
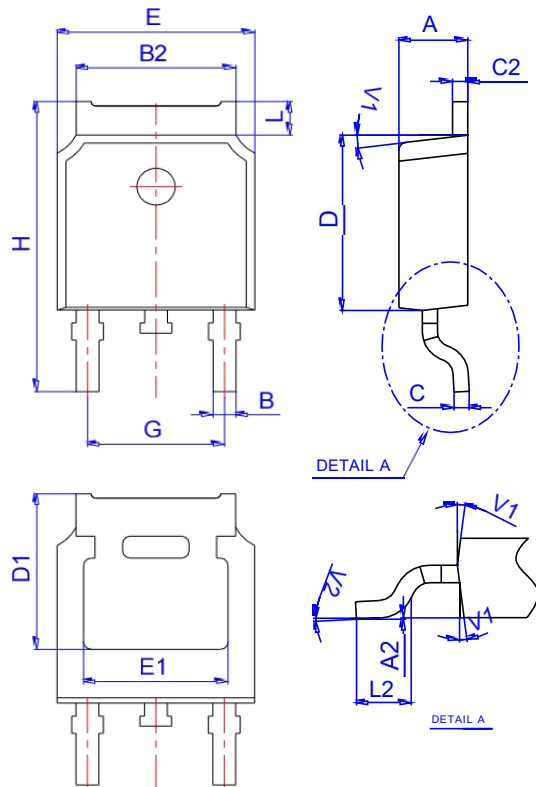


Figure 11 Normalized Maximum Transient Thermal Impedance

Package Mechanical Data: TO-252-3L



Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	2.10		2.50	0.083		0.098
A2	0		0.10	0		0.004
B	0.66		0.86	0.026		0.034
B2	5.18		5.48	0.202		0.216
C	0.40		0.60	0.016		0.024
C2	0.44		0.58	0.017		0.023
D	5.90		6.30	0.232		0.248
D1	5.30REF			0.209REF		
E	6.40		6.80	0.252		0.268
E1	4.63			0.182		
G	4.47		4.67	0.176		0.184
H	9.50		10.70	0.374		0.421
L	1.09		1.21	0.043		0.048
L2	1.35		1.65	0.053		0.065
V1		7°			7°	
V2	0°		6°	0°		6°

Package Marking and Ordering Information

Product ID	Pack	Marking	Qty(PCS)
TAPING	TO-252-3L		2500